## ECE 5317/6351

## Fall 2019

## Project

Project update date: 10/22/2019

## INSTRUCTIONS

This project is due on Monday, Dec. 9, at 5:00 p.m. (Please submit your project by slipping it under the instructor's door.) Please work individually on the project, and do not discuss it with anyone other than the instructor. Please make sure that your version of the project is the latest one that is on Blackboard by checking the "project update date" on the first page. If any corrections need to be made, a revised version of the project will be posted on Blackboard and the date will be changed.

## PROBLEM DESCRIPTION

The purpose of this project is to compare signal distortion on a microstrip line and a stripline. The microstrip and stripline geometries are shown below. The lines extends to infinity in the $z$ direction. A signal generator is attached at $z=0$ with the polarity shown. The signal generator applies a voltage signal that is

$$
v_{s}(t)=\left\{\begin{array}{cc}
1 V, & 0<t<t_{0} \\
0, & \text { otherwise }
\end{array}\right.
$$

where $t_{0}=1.0 \times 10^{-10}[\mathrm{~s}]$.

## FORMULATION AND CALCULATION

Formulate the transmission line voltage $v(z, t)$ at a point $z>0$, giving enough details to make the derivation complete. However, you do not need to re-derive anything in your write-up that is
already derived in the class notes. Note that the Fourier transform of the input voltage function can be obtained in closed form, and you should do this as part of your analysis. Then implement the numerical calculation of the voltage $v(z, t)$ using any software package that you prefer (e.g., Matlab). Please use the CAD formulas given below for all of the microstrip line calculations.

## RESULTS

## A) Frequency-Domain

1) Plot the characteristic impedance vs. frequency for both the microstrip and the stripline structures. Ignore loss for this calculation (the characteristic impedance will therefore be a real number).
2) Plot the conductor attenuation $\alpha_{c}$, the dielectric attenuation $\alpha_{d}$, and the total attenuation $\alpha$ (all in $\mathrm{np} / \mathrm{m}$ ) versus frequency, from 0 to 50 GHz , for both the microstrip and the stripline structures.

## B) Time-Domain

1) Plot the transmission-line voltage $v(z, t)$ versus $t$ for $z=1 \mathrm{~cm}, 5 \mathrm{~cm}, 10 \mathrm{~cm}, 20 \mathrm{~cm}$, and 40 cm . Account for all loss (dielectric and conductor).
2) Repeat the above plots assuming there is no dielectric or conductor loss.

Note: To remove the dielectric loss, set the loss tangent of the dielectric to be zero. To remove the conductor loss, set the conductivity of the metal to be high enough so that the metal behaves essentially as a perfect conductor.

## Validation

In part (2) of the Time-Domain results, the voltage pulse should propagate at the phase velocity $v_{p}=c / \sqrt{\varepsilon_{r}}$ without changing shape for the stripline. Hence, you know what the correct results should be for this case. Make sure that your numerical solution gives you the correct results! (Your results will exhibit the Gibbs phenomenon, however; please see the note below in the
discussion of numerical issues.) For extra validation, you can try getting results for the case of a pulse propagating on a microstrip line as shown in the class notes.

## FORMAT GUIDELINES

Your project should consist of a write-up that contains an Abstract, an Introduction section, a Formulation section, a Results section, and a Conclusions Section. You may also include a References section and an Appendix, if appropriate. The project should be done on a word processor, with the equations done in the word processor. You may use any word processor that you wish. However, it is recommended that you write the report using Microsoft Word along with MathType to do the equations. (This is how this project document was written.) For a free 30-day trial version of MathType, please visit www.mathtype.com.

The Results section should provide the results that are required, and also provide a thorough discussion of the results. All plots should be done using software such as Matlab, etc., and should look professional.

A very significant part of your grade will depend on the accuracy of your results, so you are encouraged to do as much numerical checking as possible to have confidence in your results.

Also important is the thoroughness of your discussion and your interpretation of the results.

You will also be graded on the neatness and quality of your write-up (including grammar, format, and appearance), and the quality of your results. Please use a good choice of scales and professional-looking axis labeling when you plot your results, and make sure that your plots are easy to read and look nice.

## NUMERICAL ISSUES

Numerical experimentation will probably be required to make sure that you have a sufficient limit of integration $\omega_{\max }$ for the integration variable $\omega$ in the numerical calculation of the inverse Fourier transform integral. You may also need to experiment to make sure that you have a sufficient sample density (number of integration points) when you compute the integral. You may wish to plot the integrand to help you with this. Note that the numerical integration may
require a finer sample density as the distance $z$ increases, since the integrand will oscillate faster as a function of $\omega$ as $z$ increases. It might be helpful to break up the integral from zero to $\omega_{\max }$ into several sub-intervals.

Also, be aware that you will encounter what is known as the "Gibbs phenomenon" since the input pulse has sharp edges. This means that there will be "ringing" near the edges of the pulse, even in the ideal case with no loss and no dispersion, because your numerical calculation has a finite integration limit. To read more about the Gibbs phenomenon, please visit https://en.wikipedia.org/wiki/Gibbs_phenomenon.

## PARAMETERS OF MICROSTRIP LINE

$\mathcal{E}_{r}=2.2$
$\tan \delta=0.0009$ (loss tangent of substrate)
$h=1.575[\mathrm{~mm}](62$ [mils] $)$
$w=4.83[\mathrm{~mm}]$
$t=0.0175[\mathrm{~mm}]$ (corresponding to 0.5 oz copper $/ \mathrm{ft}^{2}$ for the copper cladding)
$\sigma=3.0 \times 10^{7}[\mathrm{~S} / \mathrm{m}]$ (for both of the copper conductors, the strip and the ground plane)

Note: This substrate corresponds to Rogers 5880 material (https://rogerscorp.com/en/advanced-connectivity-solutions/rt-duroid-laminates).

Note: The characteristic impedance should be $50[\Omega]$ at 1 GHz (according to TXLINE).

## PARAMETERS OF STRIPLINE

$\varepsilon_{r}=2.2$
$\tan \delta=0.0009$ (loss tangent of substrate)
$b=3.15$ [mm] (124 [mils])
$w=2.55[\mathrm{~mm}]$
$t=0.0175[\mathrm{~mm}]$ (corresponding to 0.5 oz copper $/ \mathrm{ft}^{2}$ for the copper cladding)
$\sigma=3.0 \times 10^{7}[\mathrm{~S} / \mathrm{m}]$ (for both of the copper conductors, the strip and the ground plane)

Note: This substrate corresponds to Rogers 5880 material (https://rogerscorp.com/en/advanced-connectivity-solutions/rt-duroid-laminates).

Note: The characteristic impedance should be $50[\Omega]$ at 1 GHz (according to TXLINE).

## MICROSTRIP GEOMETRY



## STRIPLINE GEOMETRY


TOP VIEW
$\uparrow y$


## APPROXIMATE CAD DESIGN FORMULAS FOR MICROSTRIP

Note: In these formulas, $\varepsilon_{r}$ is the real part of the complex relative permittivity.

## Phase Constant

$\beta=k_{0} \sqrt{\varepsilon_{r}^{e f f}(f)}$
where the "effective relative permittivity" is

$$
\begin{aligned}
& \varepsilon_{r}^{\text {eff }}(f)=\left(\sqrt{\varepsilon_{r}^{e f f}(0)}+\frac{\sqrt{\varepsilon_{r}}-\sqrt{\varepsilon_{r}^{e f f}}(0)}{1+4 F^{-1.5}}\right)^{2} \\
& \varepsilon_{r}^{\text {eff }}(0)=\frac{\varepsilon_{r}+1}{2}+\left(\frac{\varepsilon_{r}-1}{2}\right)\left(\frac{1}{\sqrt{1+12(h / w)}}\right)-\left(\frac{\varepsilon_{r}-1}{4.6}\right)\left(\frac{t / h}{\sqrt{w / h}}\right) \quad(w / h \geq 1) \\
& F=4\left(\frac{h}{\lambda_{0}}\right) \sqrt{\varepsilon_{r}-1}\left(0.5+\left(1+0.868 \ln \left(1+\frac{w}{h}\right)\right)^{2}\right)
\end{aligned}
$$

## Characteristic Impedance

$Z_{0}(f)=Z_{0}(0)\left(\frac{\varepsilon_{r}^{\text {eff }}(f)-1}{\varepsilon_{r}^{\text {eff }}(0)-1}\right) \sqrt{\frac{\varepsilon_{r}^{\text {eff }}(0)}{\varepsilon_{r}^{\text {eff }}(f)}}$
where

$$
\begin{aligned}
& Z_{0}(0)=\frac{120 \pi}{\sqrt{\varepsilon_{r}^{\text {eff }}}(0)\left[\left(w^{\prime} / h\right)+1.393+0.667 \ln \left(\left(w^{\prime} / h\right)+1.444\right)\right]} \quad(w / h \geq 1) \\
& w^{\prime}=w+\frac{t}{\pi}\left(1+\ln \left(\frac{2 h}{t}\right)\right)
\end{aligned}
$$

## Conductor Attenuation

Note: In these formulas, $Z_{0}$ means $Z_{0}(f)$.
$\frac{w}{h} \leq \frac{1}{2 \pi}$.
$\alpha_{c}=\left(\frac{R_{s}}{h Z_{0}}\right)\left(\frac{1}{2 \pi}\right)\left[1-\left(\frac{w^{\prime}}{4 h}\right)^{2}\right]\left[1+\frac{h}{w^{\prime}}+\frac{h}{\pi w^{\prime}}\left(\ln \left(\frac{4 \pi w}{t}\right)+\frac{t}{w}\right)\right]$
$\frac{1}{2 \pi}<\frac{w}{h} \leq 2:$
$\alpha_{c}=\left(\frac{R_{s}}{h Z_{0}}\right)\left(\frac{1}{2 \pi}\right)\left[1-\left(\frac{w^{\prime}}{4 h}\right)^{2}\right]\left[1+\frac{h}{w^{\prime}}+\frac{h}{\pi w^{\prime}}\left(\ln \left(\frac{2 h}{t}\right)-\frac{t}{h}\right)\right]$
$\frac{w}{h} \geq 2:$
$\alpha_{c}=\left(\frac{R_{s}}{h Z_{0}}\right)\left[\frac{w^{\prime}}{h}+\frac{2}{\pi} \ln \left(\left(\frac{w^{\prime}}{2 h}+0.94\right) 2 \pi e\right)\right]^{-2}\left[\frac{w^{\prime}}{h}+\frac{w^{\prime} /(\pi h)}{\frac{w^{\prime}}{2 h}+0.94}\right]\left[1+\frac{h}{w^{\prime}}+\frac{h}{\pi w^{\prime}}\left(\ln \left(\frac{2 h}{t}\right)-\frac{t}{h}\right)\right]$
where
$R_{s}=\frac{1}{\sigma \delta}$
$\delta=\sqrt{\frac{2}{\omega \mu_{0} \sigma}}$ (This is the skin depth, assuming that the metal is nonmagnetic).
$w^{\prime}=w+\frac{t}{\pi}\left(1+\ln \left(\frac{2 h}{t}\right)\right)$

Note: In the term $2 \pi e$ in the last $\alpha_{c}$ formula, $e$ is the number $e$ (sometimes called "Euler's number"), $e=2.718281828$.

## Dielectric Attenuation

$\alpha_{d}=q k_{0} \sqrt{\varepsilon_{r}}\left(\frac{\tan \delta}{2}\right)$,
where the "filling factor" $q$ is
$q=\sqrt{\frac{\varepsilon_{r}}{\varepsilon_{r}^{e f f}}(f)}\left(\frac{\varepsilon_{r}^{\text {eff }}(f)-1}{\varepsilon_{r}-1}\right)$.

## APPROXIMATE CAD DESIGN FORMULAS FOR STRIPLINE

Note: In these formulas, $\varepsilon_{r}$ is the real part of the complex relative permittivity.

## Phase Constant

$\beta=k_{0} \sqrt{\varepsilon_{r}}$

## Characteristic Impedance

$Z_{0}=\left(\frac{\eta_{0}}{4 \sqrt{\varepsilon_{r}}}\right) \frac{b}{w_{e}+\frac{\ln (4)}{\pi} b}$
$\frac{w_{e}}{b}=\frac{w}{b}-\left\{\begin{array}{cc}0 & ; \text { for } \frac{w}{b} \geq 0.35 \\ \left(0.35-\frac{w}{b}\right)^{2} & ; \text { for } 0.1 \leq \frac{w}{b} \leq 0.35\end{array}\right.$

## Dielectric Attenuation

$\alpha_{d}=k^{\prime \prime} \approx \frac{k^{\prime}}{2} \tan \delta_{d} \approx \frac{k_{0} \sqrt{\varepsilon_{r}}}{2} \tan \delta_{d}$

## Conductor Attenuation

$\alpha_{c} \approx\left\{\begin{aligned}\left(2.7 \times 10^{-3}\right) \frac{4 R_{s} \varepsilon_{r} Z_{0}}{\eta_{0}(b-t)} A ; & \text { for } \sqrt{\varepsilon_{r}} Z_{0} \leq 120[\Omega] \quad \text { (wider strips) } \\ 0.16\left(\frac{R_{s}}{Z_{0} b}\right) B ; & \text { for } \sqrt{\varepsilon_{r}} Z_{0} \geq 120[\Omega] \quad \text { (narrower strips) }\end{aligned}\right.$
where
$A=1+2 \frac{w}{(b-t)}+\frac{1}{\pi}\left(\frac{b+t}{b-t}\right) \ln \left(\frac{2 b-t}{t}\right)$
$B=1+\frac{b}{\left(\frac{w}{2}+0.7 t\right)}+\left(\frac{1}{2}+0.414 \frac{t}{w}+\frac{1}{2 \pi} \ln \left(4 \pi \frac{w}{t}\right)\right)$
and
$R_{s}=\frac{1}{\sigma \delta}$
$\delta=\sqrt{\frac{2}{\omega \mu_{0} \sigma}}$ (This is the skin depth, assuming that the metal is nonmagnetic).

## REFERENCES

L. G. Maloratsky, Passive RF and Microwave Integrated Circuits, Elsevier, 2004.
I. Bahl and P. Bhartia, Microwave Solid State Circuit Design, Wiley, 2003.
R.A. Pucel, D. J. Masse,and C. P. Hartwig, "Losses in Microstrip," IEEE Trans. Microwave Theory and Techniques, pp. 342-350, June 1968.
R.A. Pucel, D. J. Masse,and C. P. Hartwig, "Corrections to 'Losses in Microstrip'," IEEE Trans. Microwave Theory and Techniques, Dec. 1968, p. 1064.

